



7A, 500V N-CHANNEL POWER MOSFET

DESCRIPTION

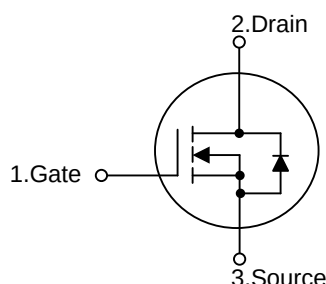
The UTC **7N50-TC2** is a N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **7N50-TC2** is generally applied in high efficiency switch mode power supplies, active power factor correction and electronic lamp ballasts based on half bridge topology.

FEATURES

- * $R_{DS(ON)} \leq 1.3 \Omega$ @ $V_{GS}=10V$, $I_D=3.5A$
- * High Switching Speed
- * 100% Avalanche Tested

SYMBOL

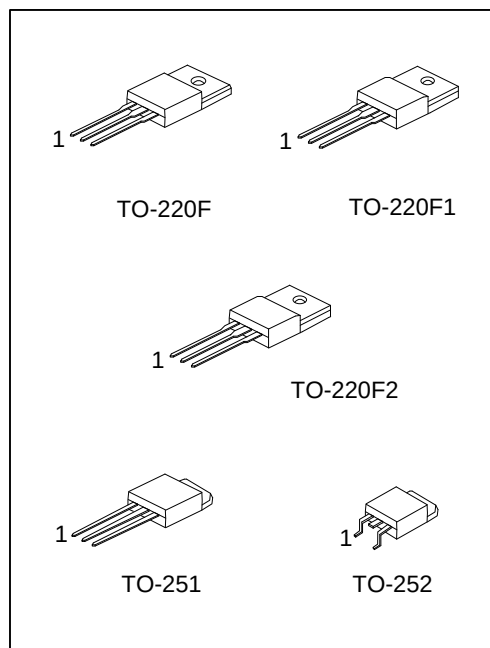


ORDERING INFORMATION

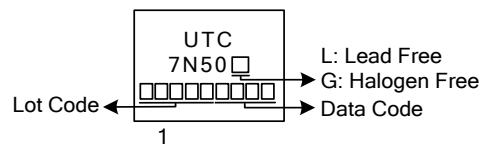
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
7N50L-TF1-T	7N50G-TF1-T	TO-220F1	G	D	S	Tube
7N50L-TF2-T	7N50G-TF2-T	TO-220F2	G	D	S	Tube
7N50L-TF3-T	7N50G-TF3-T	TO-220F	G	D	S	Tube
7N50L-TM3-T	7N50G-TM3-T	TO-251	G	D	S	Tube
7N50L-TN3-R	7N50G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

7N50G-TF1-T (1)Packing Type (2)Package Type (3)Green Package		(1) T: Tube, R: Tape Reel (2) TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2 TM3: TO-251, TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	7	A
	Pulsed (Note 2)	I_{DM}	14	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	81	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.1	V/ns
Power Dissipation	TO-220F/TO-220F1 TO-220F2	P_D	36	W
	TO-251/TO-252		50	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 1.0\text{mH}$, $I_{AS} = 12.7\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$

4. $I_{SD} \leq 7.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^{\circ}\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220F/TO-220F1 TO-220F2	θ_{JA}	62.5	$^{\circ}\text{C}/\text{W}$
	TO-251/TO-252		110	$^{\circ}\text{C}/\text{W}$
Junction to Case	TO-220F/TO-220F1 TO-220F2	θ_{JC}	3.66	$^{\circ}\text{C}/\text{W}$
	TO-251/TO-252		2.5 (Note)	$^{\circ}\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

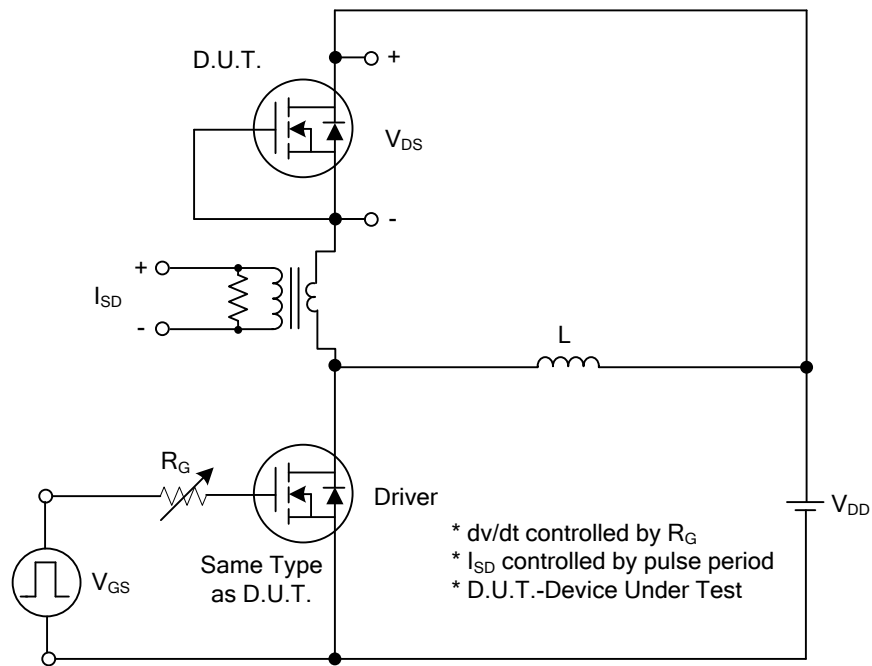
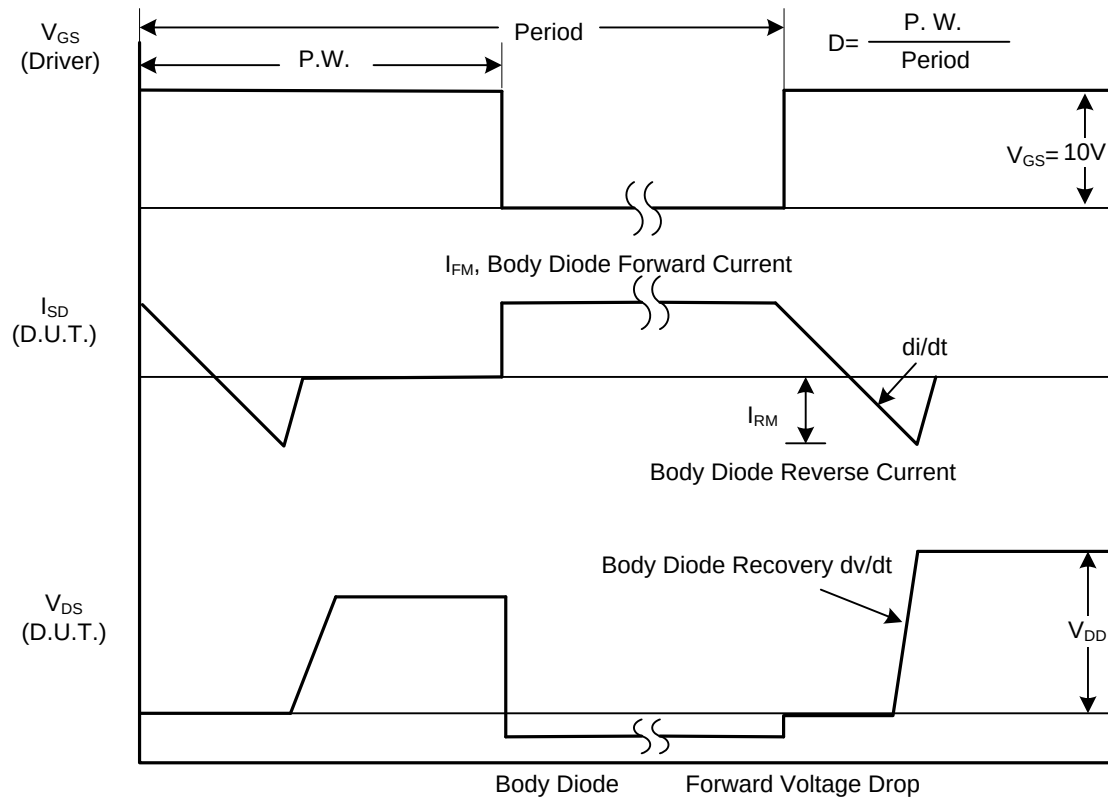
■ **ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	500			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =500V, V _{GS} =0V			10	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =3.5A			1.3	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		720		pF
Output Capacitance		C _{OSS}			76		pF
Reverse Transfer Capacitance		C _{RSS}			3.5		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =400V, V _{GS} =10V, I _D =7.0A, I _G =1mA (Note 1, 2)		14.4		nC
Gate to Source Charge		Q _{GS}			4.5		nC
Gate to Drain Charge		Q _{GD}			1.7		nC
Turn-ON Delay Time (Note 1)		t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =7.0A, R _G =25Ω (Note 1, 2)		6		ns
Rise Time		t _R			16		ns
Turn-OFF Delay Time		t _{D(OFF)}			38		ns
Fall-Time		t _F			24		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				7	A
Maximum Body-Diode Pulsed Current (Note 1)		I _{SM}				14	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =7.0A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time		t _{rr}	I _S =7.0A, V _{GS} =0V,		260		ns
Body Diode Reverse Recovery Charge		Q _{rr}	dl _F /dt=100A/μs		4.9		μC

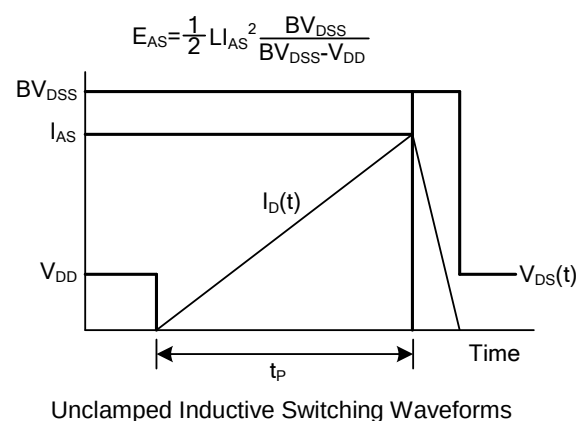
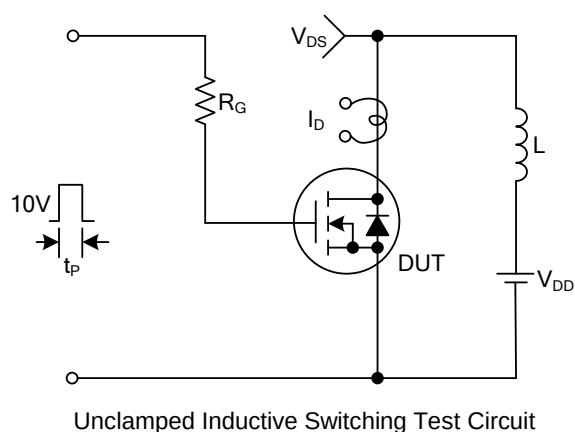
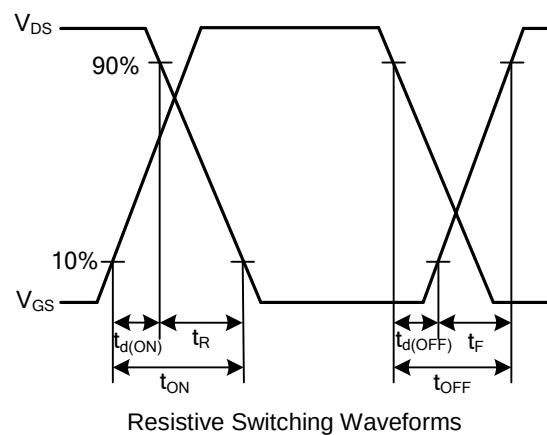
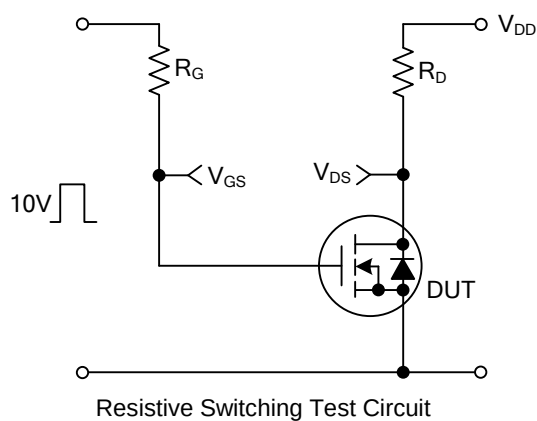
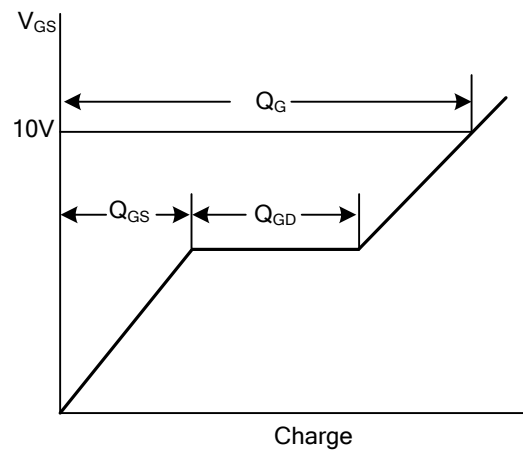
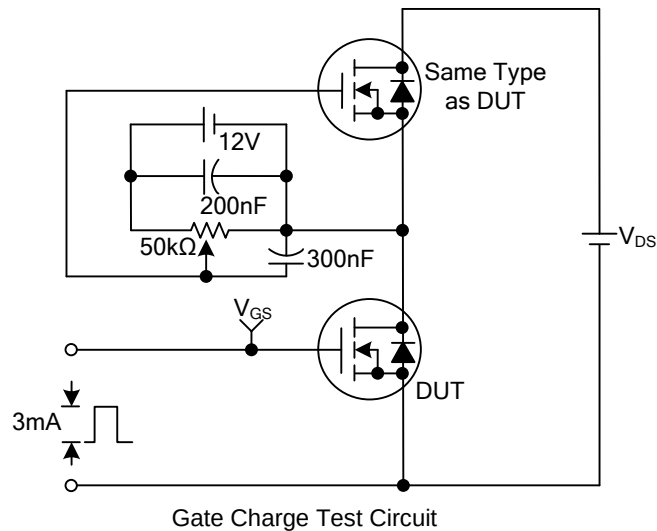
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

Peak Diode Recovery dv/dt Test CircuitPeak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS



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